



(19)

(11) Publication number: **2001**

Generated Document.

**PATENT ABSTRACTS OF JAPAN**(21) Application number: **2000153142**(51) Intl. Cl.: **H01L 21/304 B24B 37/00**(22) Application date: **24.05.00**

(30) Priority:	(71) Applicant: <b>MATSUSHITA ELECTR LTD</b>
(43) Date of application publication: <b>30.11.01</b>	(72) Inventor: <b>YOSHIDA HIDEAKI</b>
(84) Designated contracting states:	(74) Representative:

**(54) POLISHING PAD,  
CHEMICAL MECHANICAL  
POLISHING METHOD, AND  
METHOD OF  
MANUFACTURING  
SEMICONDUCTOR DEVICE**

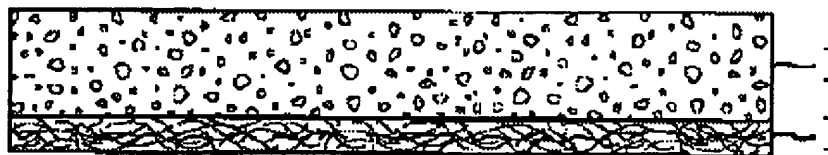
(57) Abstract:

PROBLEM TO BE SOLVED: To enable a polishing pad to entirely satisfy the polishing rate, the in-plane uniformity of polishing rate, flattening property, defect characteristic, etc., when the pad is used for the chemical mechanical polishing of a film to be polished.

SOLUTION: The polishing pad 101 which is used in the chemical mechanical polishing on the film to be polished which is stuck to a turntable and is composed of an insulating film or conductive film has a laminated structure composed of a nonwoven fabric section 101b provided on the turntable side, and a foamed polyurethane section 101a provided on the film to be polished

side. The thickness of the foamed polyurethane section 101a is made larger than that of the nonwoven fabric section 101b.

COPYRIGHT: (C)2001,JPO



BEST AVAILABLE COPY